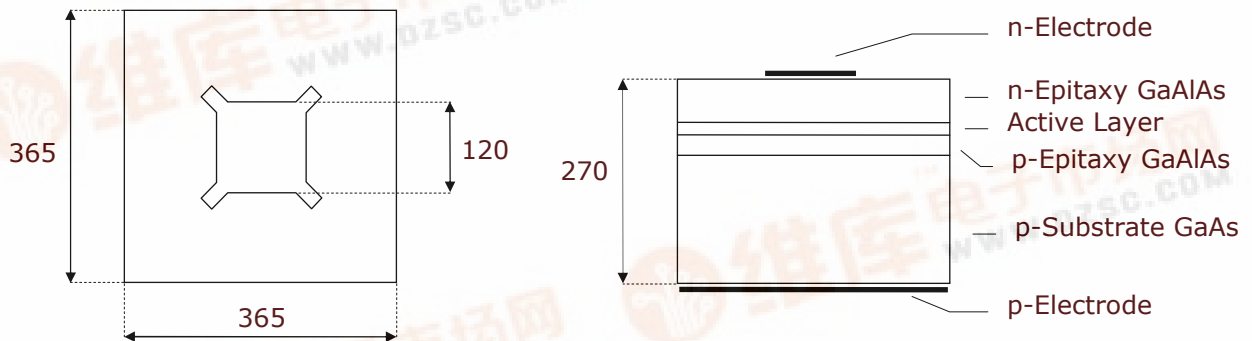


**INFRA-RED**

**Item No.: 126124**

1. This specification applies to GaAlAs / GaAs Chips (substrate removed)
2. Structure
  - 2.1 Mesa structure
  - 2.2 Electrodes
 

p-side (anode)	Au alloy
n-side (cathode)	Au alloy
3. Outlines (dimensions in microns)



Wire bond contacts can also be square

4. Electrical and optical characteristics (T=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Forward voltage	$V_F$	$I_F = 20 \text{ mA}$		1,30	1,60	V
Reverse voltage	$V_R$	$I_R = 5 \mu\text{A}$			10	V
output Power *	$\Phi_e$	$I_F = 20 \text{ mA}$	0,9	1,2		mW
Switching time	$t_r, t_f$	$I_F = 20 \text{ mA}$		40		ns
Peak wavelength	$\lambda_p$	$I_F = 20 \text{ mA}$		860		nm

Power measurement at OSA on gold plate

5. Packing

Dice on adhesive film with 1) wire bond side on top  
2) back contact on top

6. Labeling

Type	Lot No.	$\Phi_e$ typ min max	Quantity
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